

CLAIMS

1. A structure comprising:
a semiconductor die having a source bond pad and a destination bond pad attached
to a top surface of said semiconductor die;
5 a stud bump, said stud bump being situated on said destination bond pad;
a bonding wire providing a connection between said source bond pad and said stud
bump.
2. The structure of claim 1 wherein said source bond pad is a first terminal of
10 an inductor and said destination bond pad is a second terminal of said inductor.
3. The structure of claim 1 wherein a first end of said bonding wire is ball
bonded to said source bond pad.
- 15 4. The structure of claim 1 wherein a second end of said bonding wire is stitch
bonded to said stud bump.
5. The structure of claim 1 wherein said source bond pad is a specialized
semiconductor die bond pad.
- 20 6. The structure of claim 1 wherein said destination bond pad is a specialized
semiconductor die bond pad.

7. The structure of claim 2 wherein an inductance of said inductor is increased by increasing a loop height of said bonding wire, and wherein said inductance of said inductor is decreased by decreasing said loop height of said bonding wire.

5 8. A structure comprising:
a semiconductor die having a first semiconductor die bond pad, a second semiconductor die bond pad, and a third semiconductor die bond pad attached to a top surface of said semiconductor die;

10 a first conductor providing a connection between said first semiconductor die bond pad and said second semiconductor die bond pad;

a bonding wire providing a connection between said second semiconductor die bond pad and said third semiconductor die bond pad.

15 9. The structure of claim 8 further comprising a stud bump situated on said second semiconductor die bond pad, wherein said bonding wire provides said connection between said stud bump and said third semiconductor die bond pad.

10. The structure of claim 8 wherein said first semiconductor die bond pad is a first terminal of an inductor.

20 11. The structure of claim 8 wherein said second semiconductor die bond pad is a destination bond pad and said third semiconductor die bond pad is a source bond pad.

12. The structure of claim 8 wherein said first, second, and third semiconductor die bond pads are specialized semiconductor die bond pads.

13. The structure of claim 8 further comprising a second conductor provides a connection between said third semiconductor die bond pad a fourth semiconductor die bond pad.

14. The structure of claim 10 wherein an inductance of said inductor is increased by increasing a loop height of said bonding wire, and wherein said inductance of said inductor is decreased by decreasing said loop height of said bonding wire.

15. A method for fabricating an inductor, said method comprising steps of:
fabricating a source bond pad and a destination bond pad on a top surface of a semiconductor die;
forming a stud bump on said destination bond pad;
bonding a first end of a bonding wire to said source bond pad;
bonding a second end of said bonding wire to said stud bump;
said source bond pad being a first terminal of said inductor and said destination bond pad being a second terminal of said inductor.

16. The method of claim 15 wherein said first end of said bonding wire is ball bonded to said source bond pad.

17. The method of claim 15 wherein said second end of said bonding wire is stitch bonded to said stud bump.

18. The method of claim 15 wherein said source bond pad is a specialized
5 semiconductor die bond pad.

19. The method of claim 15 wherein said destination bond pad is a specialized semiconductor die bond pad.

10 20. The method of claim 15 wherein an inductance of said inductor is increased by increasing a loop height of said bonding wire, and wherein said inductance of said inductor is decreased by decreasing said loop height of said bonding wire.